

Product Summary

BVDSS	R_{DSON} Max	I_D T_C = +25°C
60V	4.5mΩ @ V _{GS} = 10V	125A
	6.5mΩ @ V _{GS} = 4.5V	108A

Description and Applications

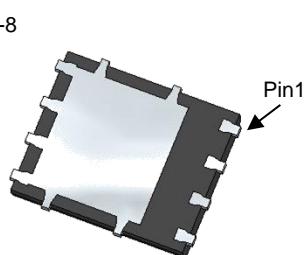
This MOSFET is designed to minimize the on-state resistance (R_{DSON}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- High Frequency Switching
- Synchronized Rectification
- DC-DC Converters

Site1:



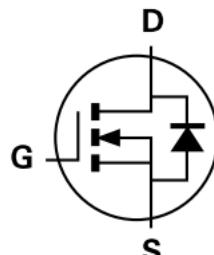
Top View



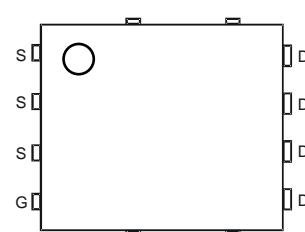
Bottom View

Mechanical Data

- Case: PowerDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ⑥3
- Weight: 0.097 grams (Approximate)

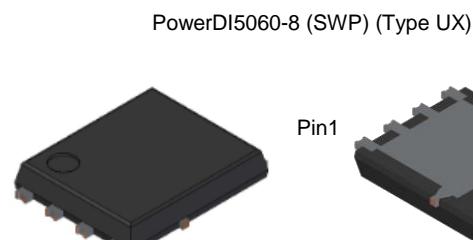


Internal Schematic



Top View
Pin Configuration

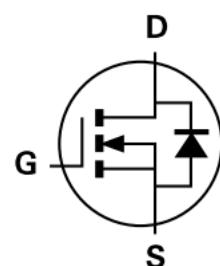
Site2:



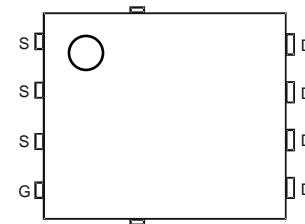
Top View



Bottom View



Internal Schematic



Top View
Pin Configuration

Notes:

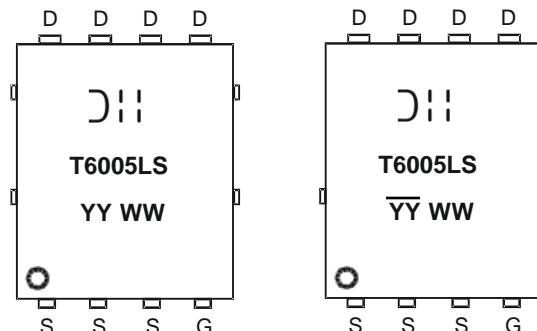
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

PowerDI is a registered trademark of Diodes Incorporated.

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6005LPS-13	PowerDI5060-8	2,500/Tape & Reel
DMT6005LPS-13	PowerDI5060-8 (SWP) (Type UX)	2,500/Tape & Reel

Note: 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information


DII = Manufacturer's Marking
 T6005LS = Product Type Marking Code
 YYWW or YYWW = Date Code Marking
 YY or YY = Year (ex: 21 = 2021)
 WW = Week (01 to 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current (Note 5)	I_D	18.4	A
		14.7	
Continuous Drain Current (Note 6)	I_D	125	A
		100	
Maximum Continuous Body Diode Forward Current (Note 6)	I_S	125	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	500	A
Avalanche Current, L = 1mH	I_{AS}	14.8	A
Avalanche Energy, L = 1mH	E_{AS}	98	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^\circ\text{C}$	P_D	2.6
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	47	$^\circ\text{C}/\text{W}$
Total Power Dissipation (Note 6)	$T_C = +25^\circ\text{C}$	P_D	125
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	1	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 6. Thermal resistance from junction to soldering point (on the exposed drain pad).

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$\text{V}_{\text{GS}} = 0\text{V}$, $\text{I}_D = 1\text{mA}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$\text{V}_{\text{DS}} = 48\text{V}$, $\text{V}_{\text{GS}} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$\text{V}_{\text{GS}} = \pm 20\text{V}$, $\text{V}_{\text{DS}} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$\text{V}_{\text{GS(TH)}}$	1	—	3	V	$\text{V}_{\text{DS}} = \text{V}_{\text{GS}}$, $\text{I}_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$\text{R}_{\text{DS(ON)}}$	—	3.5	4.5	$\text{m}\Omega$	$\text{V}_{\text{GS}} = 10\text{V}$, $\text{I}_D = 50\text{A}$
		—	5	6.5		$\text{V}_{\text{GS}} = 4.5\text{V}$, $\text{I}_D = 12.5\text{A}$
Diode Forward Voltage	V_{SD}	—	0.9	—	V	$\text{V}_{\text{GS}} = 0\text{V}$, $\text{I}_S = 50\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	2,962	—	pF	$\text{V}_{\text{DS}} = 30\text{V}$, $\text{V}_{\text{GS}} = 0\text{V}$, $f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	965.2	—		
Reverse Transfer Capacitance	C_{rss}	—	59.8	—		
Gate Resistance	R_g	—	0.66	—	Ω	$\text{V}_{\text{DS}} = 0\text{V}$, $\text{V}_{\text{GS}} = 0\text{V}$, $f = 1\text{MHz}$
Total Gate Charge ($\text{V}_{\text{GS}} = 10\text{V}$)	Q_g	—	47.1	—	nC	$\text{V}_{\text{DD}} = 30\text{V}$, $\text{I}_D = 50\text{A}$
Total Gate Charge ($\text{V}_{\text{GS}} = 4.5\text{V}$)	Q_g	—	23.1	—		
Gate-Source Charge	Q_{gs}	—	10.2	—		
Gate-Drain Charge	Q_{gd}	—	12.5	—		
Turn-On Delay Time	$\text{t}_{\text{D(ON)}}$	—	8.3	—	ns	$\text{V}_{\text{DD}} = 30\text{V}$, $\text{V}_{\text{GS}} = 10\text{V}$, $\text{I}_D = 30\text{A}$, $\text{R}_G = 3.3\Omega$
Turn-On Rise Time	t_r	—	9.4	—		
Turn-Off Delay Time	$\text{t}_{\text{D(OFF)}}$	—	22	—		
Turn-Off Fall Time	t_f	—	8.9	—		
Body Diode Reverse Recovery Time	t_{RR}	—	40.4	—	ns	$\text{I}_F = 30\text{A}$, $\text{di/dt} = 100\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	Q_{RR}	—	49.7	—	nC	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

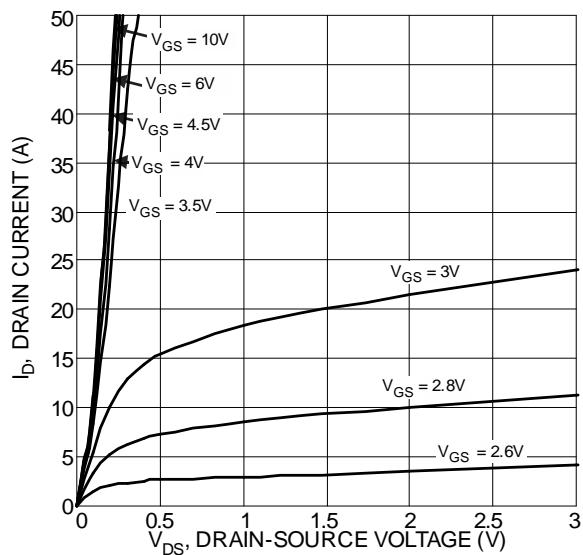


Figure 1 Typical Output Characteristic

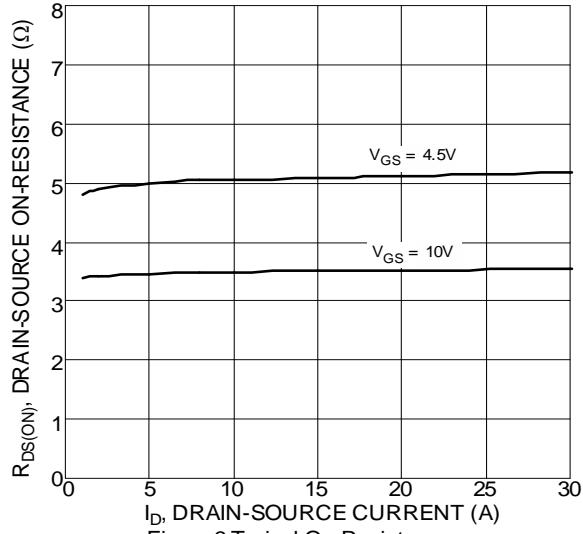


Figure 3 Typical On-Resistance vs.
Drain Current and Gate Voltage

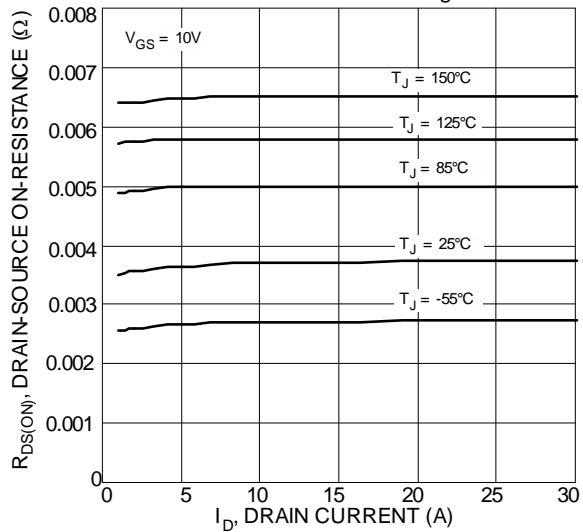


Figure 5 Typical On-Resistance vs.
Drain Current and Temperature

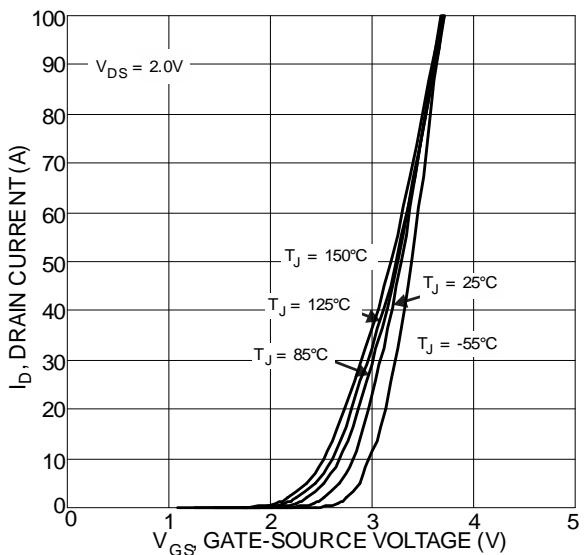


Figure 2 Typical Transfer Characteristics

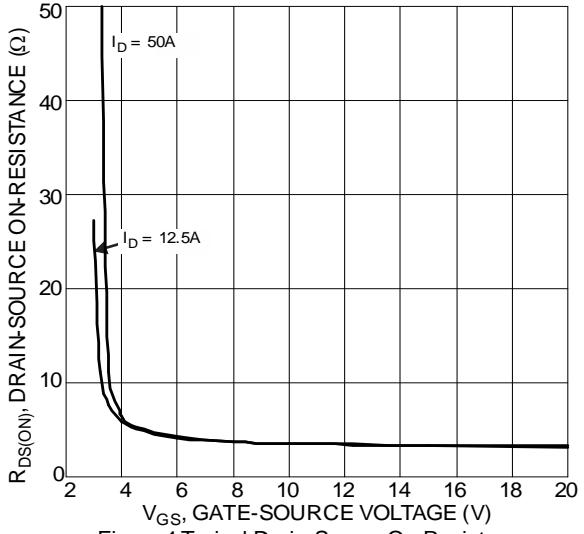


Figure 4 Typical Drain-Source On-Resistance
vs. Gate-Source Voltage

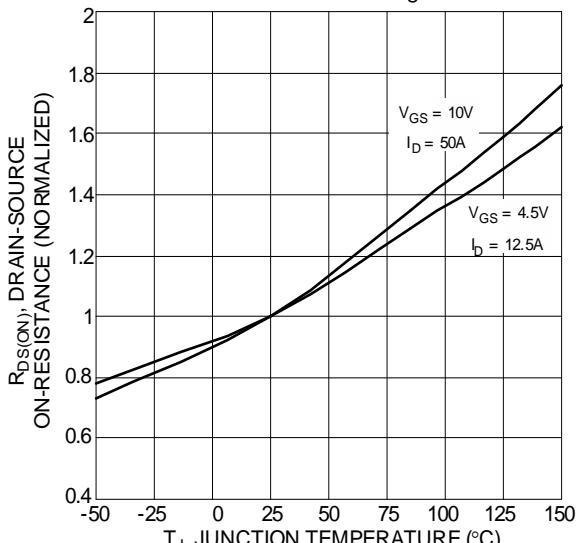


Figure 6 On-Resistance Variation with Temperature

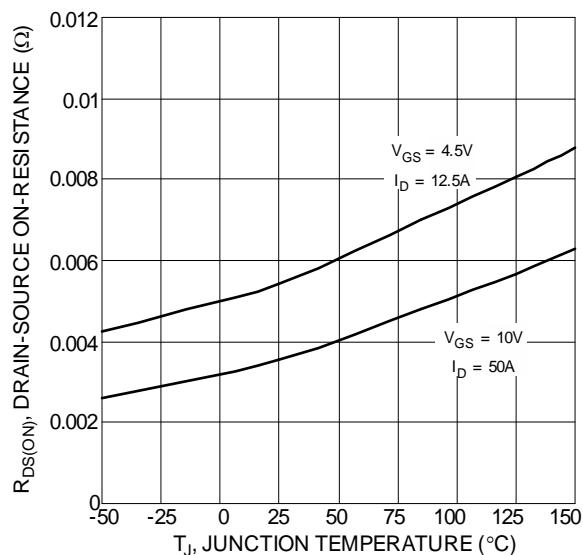


Figure 7 On-Resistance Variation with Temperature

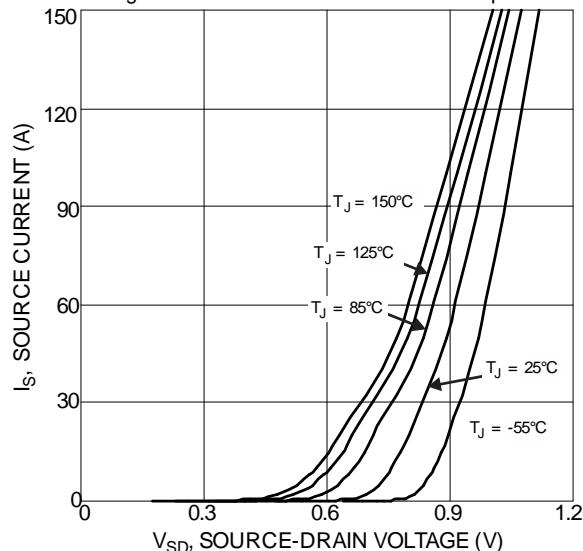


Figure 9 Diode Forward Voltage vs. Current

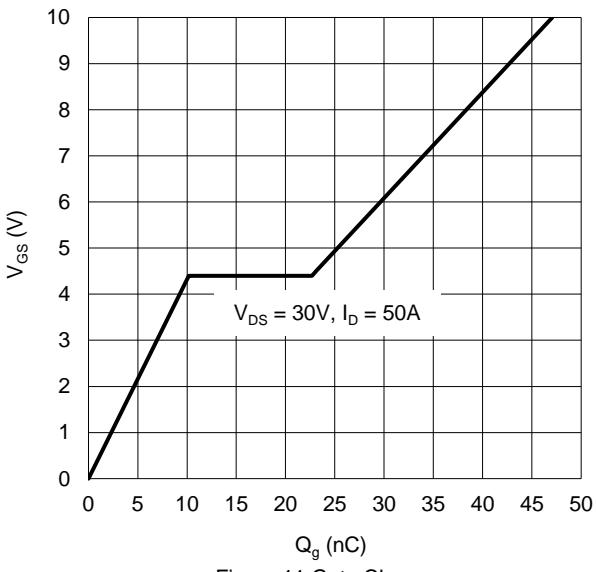


Figure 11 Gate Charge

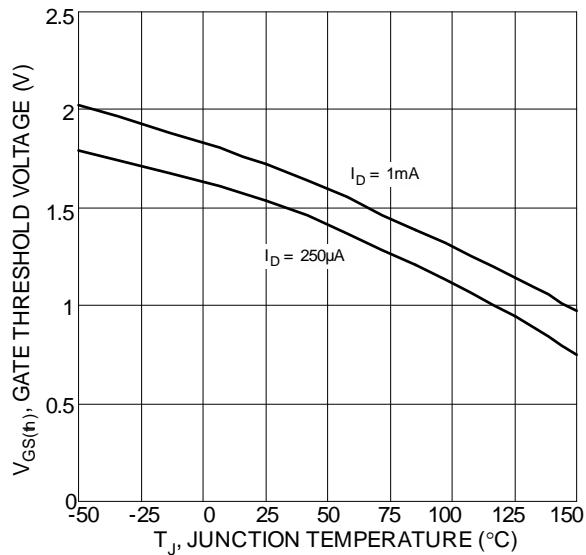


Figure 8 Gate Threshold Variation vs. Junction Temperature

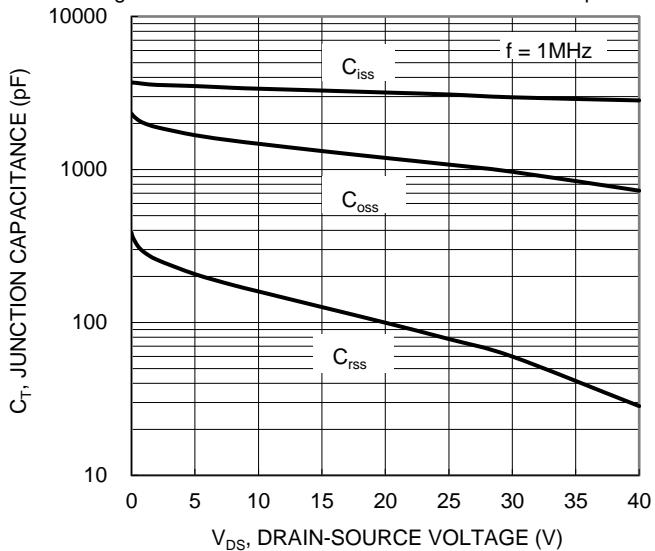


Figure 10 Typical Junction Capacitance

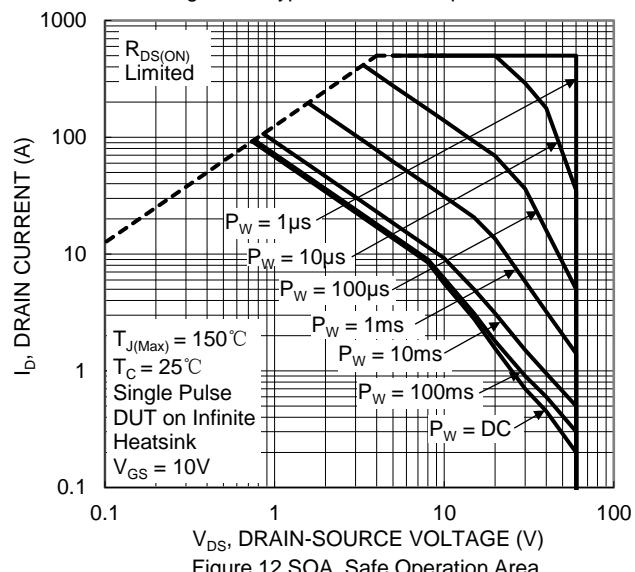


Figure 12 SOA, Safe Operation Area

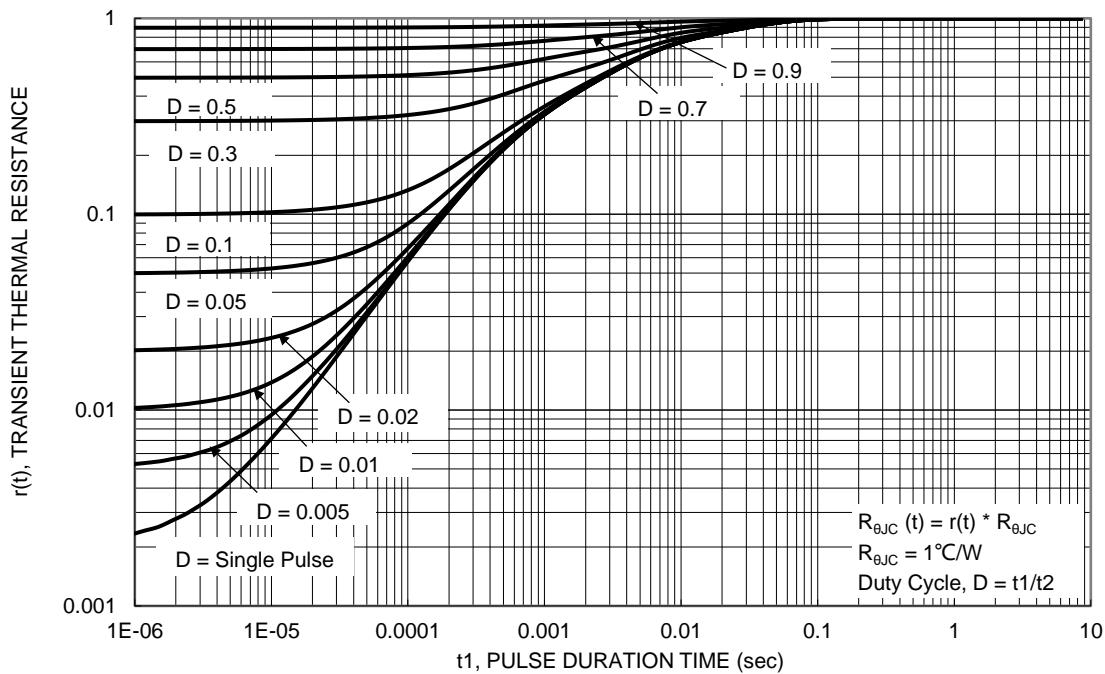
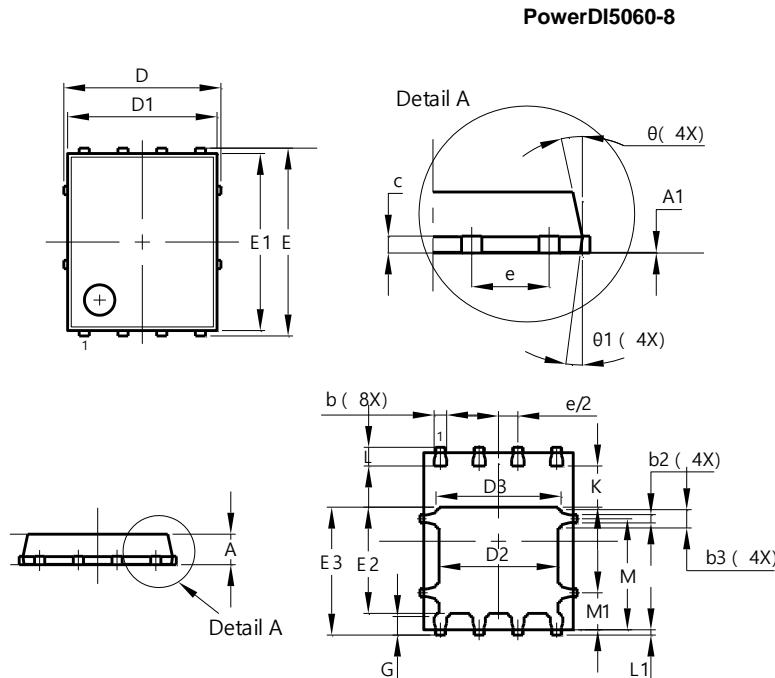


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site1:

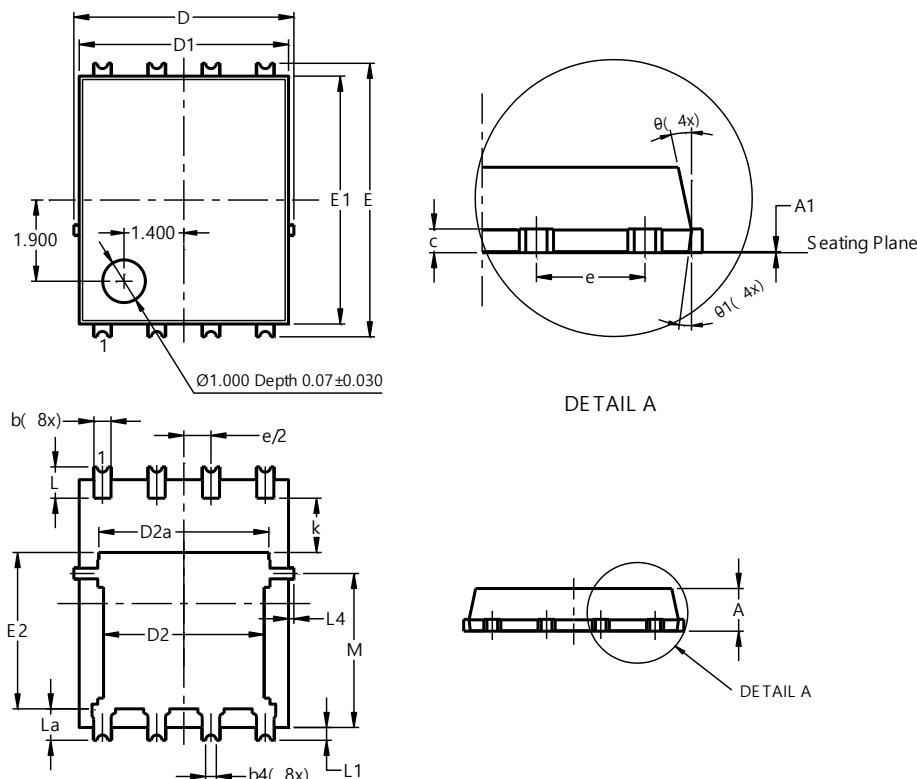


PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	—
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	—	—
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
Θ	10°	12°	11°
Θ1	6°	8°	7°

All Dimensions in mm

Site2:

PowerDI5060-8 (SWP) (Type UX)



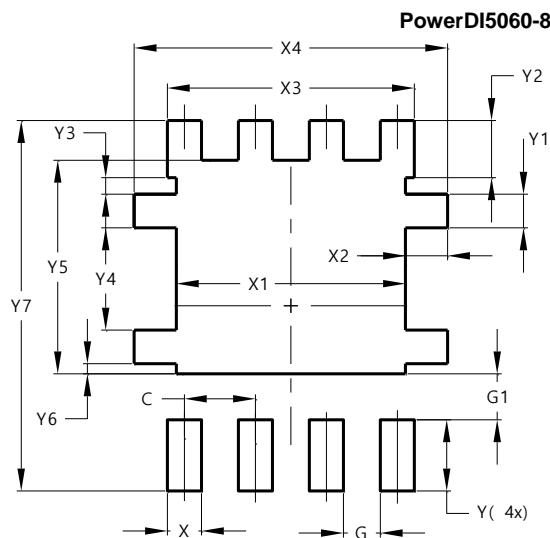
PowerDI5060-8 (SWP) (Type UX)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	—
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
K	1.05	—	—
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
Θ	10°	12°	11°
Θ1	6°	8°	7°

All Dimensions in mm

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

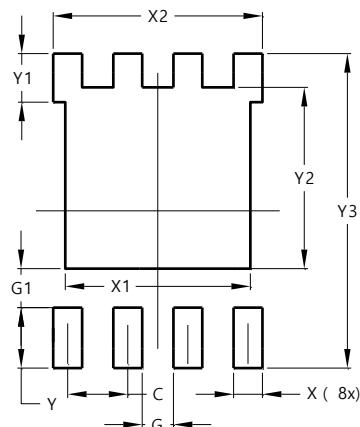
Site1:



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site2:

PowerDI5060-8 (SWP) (Type UX)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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